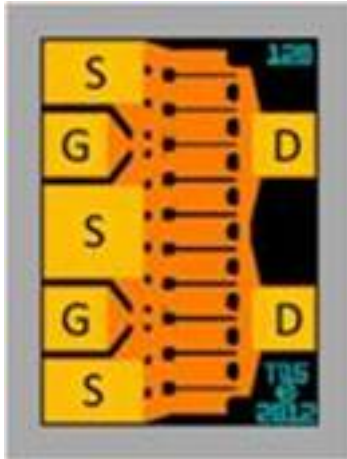


RFMW Introduces 1200-Micron Discrete FET from TriQuint Semiconductor

WDD Staff



[RFMW](#) [1] (San Jose, CA) has announced design and sales support for TriQuint Semiconductor's TGF2120, a discrete 1200-Micron GaAs pHEMT FET. Available in a 0.41 x 0.54 x 0.10mm chip suitable for eutectic die attach, the TGF2120 is constructed without via holes thereby allowing for self-biasing and eliminating the need for a negative supply voltage. Applications include military, hi-rel defense and aerospace, test and measurement and commercial, broadband amplifiers up to K-band where high efficiency and linearity are required. The TGF2120 is part of a family of high-efficiency pHEMT power FETs providing a broad selection of output powers. Features include:

- 0.25um pHEMT design optimizes power and efficiency at high drain bias operating conditions.
- 31dBm P1dB with 11dB associated gain.
- Power added efficiency (PAE) of 57%.
- Silicon nitride, protective overcoat layer provides a level of environmental robustness and scratch protection.

For more information, visit www.rfmw.com [1].

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<http://www.wirelessdesignmag.com/product-releases/2013/06/rfmw-introduces-1200-micron-discrete-fet-triquint-semiconductor>

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